E 4.20 Introduction to Digital Integrated Circuit Design

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Aims and Objectives

- Understand how full-custom VLSI chips are designed
 - Different design styles and technologies
 - Design abstractions and hierarchies
 - Partitioning and architecture
- Learn to design digital IC circuits
 - Static and dynamic logic
 - Sequential logic in IC
 - Datapaths and memories
 - Testing and design-for-test
- Learn CAD tools for IC designs
 - Layout of full-custom CMOS IC's using Electric
 - Simulation using SPICE
 - Simulation using logic simulators: IRSIM & Verilog or VHDL
 - Other design verification tools
- Have fun!

Recommended Books

- Rabaey, J. et al "Digital Integrated Circuits: A Design Perspective" 2nd Ed. ISBN: 0131207644 (16 January, 2003) Publisher: Prentice Hall. (£45)
- Weste, N. H. E., and Harris, D. "CMOS VLSI Design" 3rd Edition, ISBN 0-321-14901-7, Addison-Wesley, 2005. (£66) updated classic
- Smith, M.J.S. 1997. "Application-Specific Integrated Circuits". Reading, MA: Addison-Wesley, 1026 p. ISBN 0-201-50022-1.
 - Good book and bargain buy (£25 £45). Well written and worth buying.
- Glasser, L. A., and D. W. Dobberpuhl. 1985. "The Design and Analysis of VLSI Circuits". Reading, MA: Addison-Wesley, 473 p. ISBN 0-201-12580-3.
 - Detailed analysis of circuits, but largely for nMOS (Hard to find).
- Mead, C. A., and L. A. Conway. 1980. "Introduction to VLSI Systems". Reading, MA: Addison-Wesley, 396 p. ISBN 0-201-04358-0.
 - The first textbook in this subject, included for historical value only.

Supporting Material

- Reading material each week to support lectures
- Clearly defined targets
- Reference to textbook if relevant
- Consult my course web-page:

http://www.ee.ic.ac.uk/pcheung/teaching/ee4_asic/

Assessment, Practical work, Project

- Course work designing a chip in a group (3-4 people) 25%
- May examination (open-book) 75%
- Spend first 4 weeks learning CAD tools (Electric, IRSIM, SPICE)
- Spend the remain weeks working in small group to design a chip
- Deadline for completing lab work: Last day of Autumn term
- Deadline for report: Second Monday of Spring term
- Report (one per group) should include:
 - description of circuit designed (full schematic and layout)
 - block diagram showing different module in chip
 - plot of the entire chip
 - evidence that it works (from simulation plots)
 - test strategy and testbench
 - a description of contribution from each member, signed by all!

Topic 1

Introduction & Trends

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(Weste&Harris Ch 1; Rabaey Ch1)

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ASIC and all that! (based on slides by M. Smith)

- An **ASIC** ("a-sick") is an **application-specific integrated circuit**
- ♦ A gate equivalent is a NAND gate F = A B, or four transistors
- History of integration:
 - **small-scale integration** (**SSI**, ~10 gates per chip, 60's)
 - medium-scale integration (MSI, ~100–1000 gates per chip, 70's)
 - large-scale integration (LSI, ~1000–10,000 gates per chip, 80's)
 - very large-scale integration (VLSI, ~10,000–100,000 gates per chip, 90's)
 - ultra-large scale integration (ULSI, ~1M–10M gates per chip)
- History of technology:
 - **bipolar technology** and **transistor-transistor logic** (TTL) preceded ...
 - metal-oxide-silicon (MOS) technology because it was difficult to make metal-gate n-channel MOS (nMOS or NMOS)
 - the introduction of **complementary MOS** (CMOS) greatly reduced power

+ ASIC and all that!

- The feature size is the smallest shape you can make on a chip and is measured in λ or lambda
- Origin of ASICs:
 - standard parts initially used to design microelectronic systems
 - gradually replaced with a combination of glue logic, custom ICs, dynamic random-access memory (DRAM) and static RAM (SRAM)
- Key conferences: The IEEE Custom Integrated Circuits Conference (CICC) and IEEE International ASIC Conference document the development of ASICs
- Application-specific standard products (ASSPs) are a cross between standard parts and ASICs

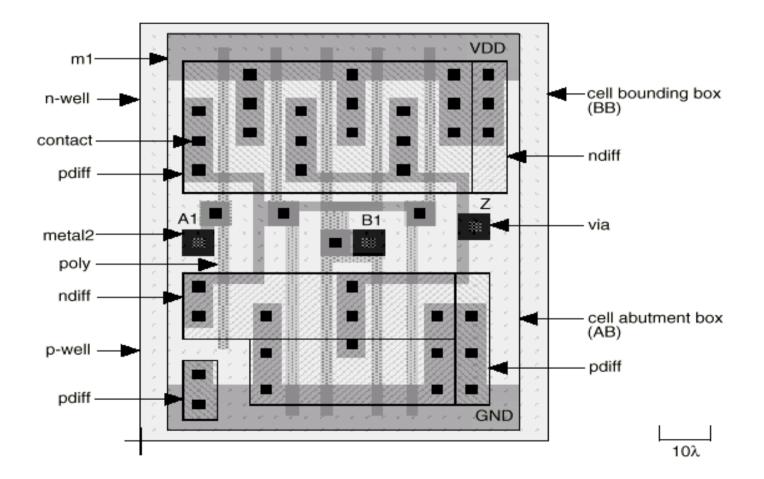
Full-custom ASIC

- All mask layers are customized in a full-custom ASIC.
- It only makes sense to design a full-custom IC if there are no libraries available.
- Full-custom offers the highest performance and lowest part cost (smallest die size) with the disadvantages of increased design time, complexity, design expense, and highest risk.
- Microprocessors were exclusively full-custom, but designers are increasingly turning to semicustom ASIC techniques in this area too.
- Other examples of full-custom ICs or ASICs are requirements for high -voltage (automobile), analog/digital (communications), or sensors and actuators.

Standard-Cell–Based ASICs

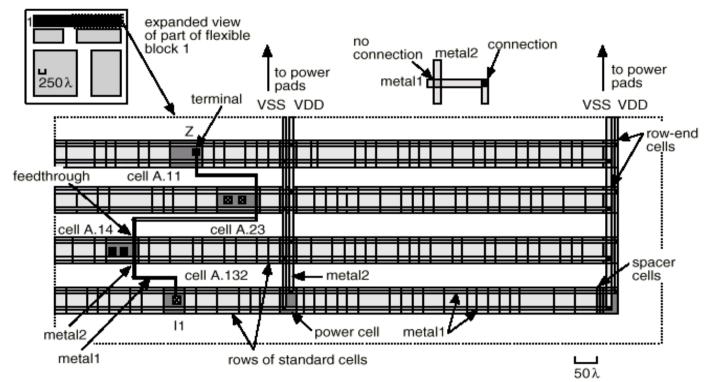
- A cell-based ASIC (CBIC—"sea-bick") Standard cells ______ standard-cell Possibly megacells, megafunctions, fullarea custom blocks, system-level macros (SLMs), fixed blocks, cores, or Functional Standard Blocks (FSBs) fixed blocks All mask layers are customized—transistors and interconnect Custom blocks can be embedded 0.02in 700000000000000000000000 500 um Manufacturing lead time is about eight weeks.
 - In datapath (DP) logic we may use a datapath compiler and a datapath library. Cells such as arithmetic and logical units (ALUs) are pitch-matched to each other to improve timing and density.

Full-custom Standard Cell



Looking down on the layout of a standard cell from a standard-cell library

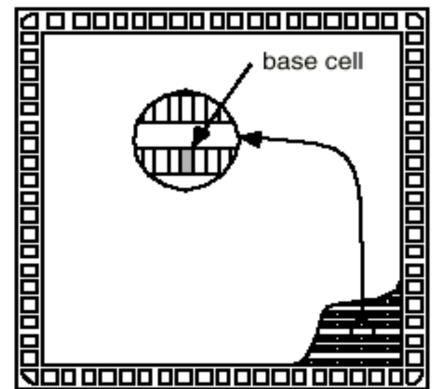
Cell-based IC



- Routing a CBIC (cell-based IC)
 - A "wall" of standard cells forms a flexible block
 - metal2 may be used in a feedthrough cell to cross over cell rows that use metal1 for wiring
 - Other wiring cells: **spacer cells**, **row-end cells**, and **power cells**

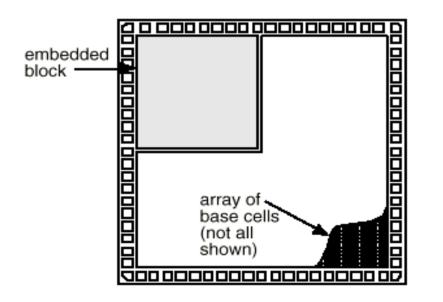
Gate-Array–Based ASICs

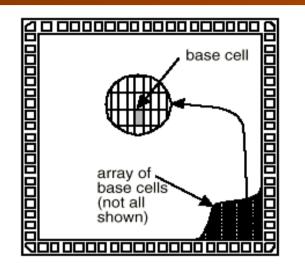
- A gate array, masked gate array, MGA, or prediffused array uses macros (books) to reduce turnaround time and comprises a base array made from a base cell or primitive cell. There are three types:
 - Channeled gate arrays
 - Channelless gate arrays
 - Structured gate arrays
- A channeled gate array
 - Only the interconnect is customized
 - The interconnect uses predefined spaces between rows of base cells
 - Manufacturing lead time is between two days and two weeks



Gate-Array–Based ASICs (con't)

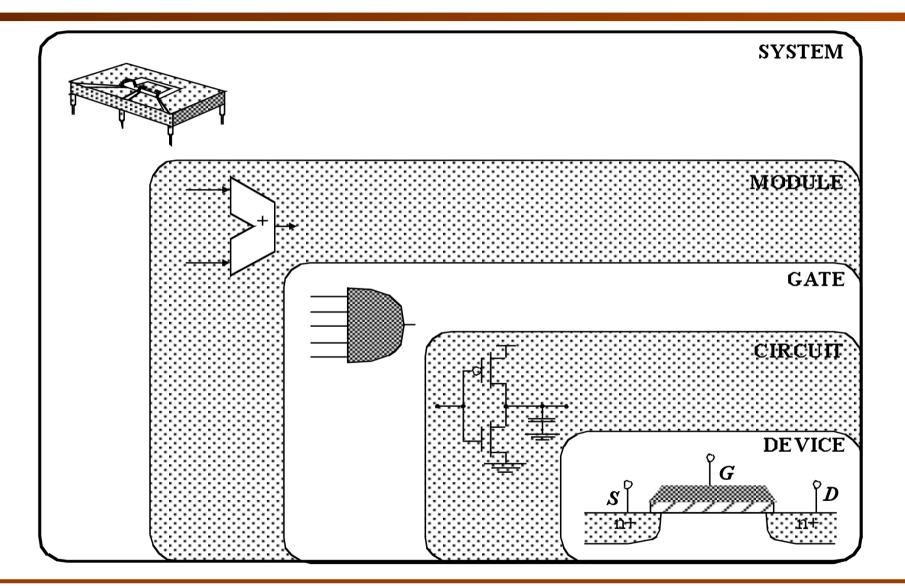
- A channelless gate array (channel -free gate array, sea-of-gates array, or SOG array)
 - Only some (the top few) mask layers are customized — the interconnect
 - Manufacturing lead time is between two days and two weeks.





- An **embedded gate array** or **structured gate array** (masterslice or masterimage)
 - Only the interconnect is customized
 - Custom blocks (the same for each design) can be embedded
 - Manufacturing lead time is between two days and two weeks.

Design Abstraction Levels

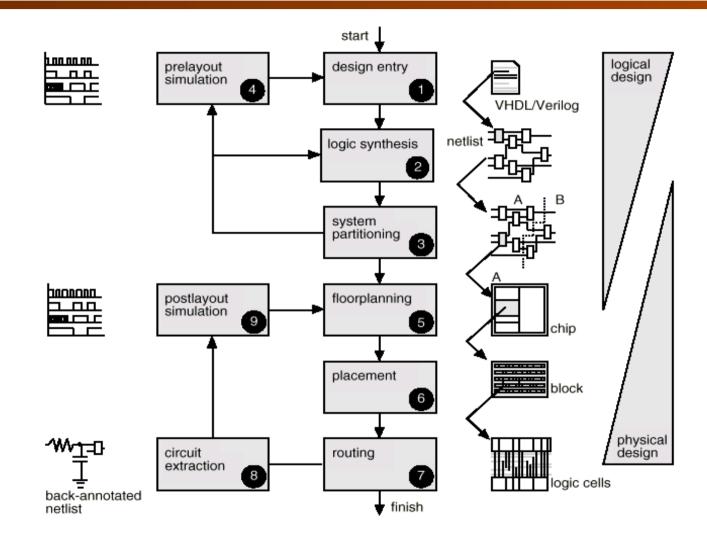


Design Flow

A **design flow** is a sequence of steps to design an ASIC

- Design entry. Using a hardware description language (HDL) or schematic entry.
- Logic synthesis. Produces a netlist—logic cells and their connections.
- **System partitioning**. Divide a large system into ASIC-sized pieces.
- **Pre-layout simulation**. Check to see if the design functions correctly.
- **Floorplanning**. Arrange the blocks of the netlist on the chip.
- Placement. Decide the locations of cells in a block.
- **Routing**. Make the connections between cells and blocks.
- Extraction. Determine the resistance and capacitance of the interconnect.
- Postlayout simulation. Check to see the design still works with the added loads of the interconnect.

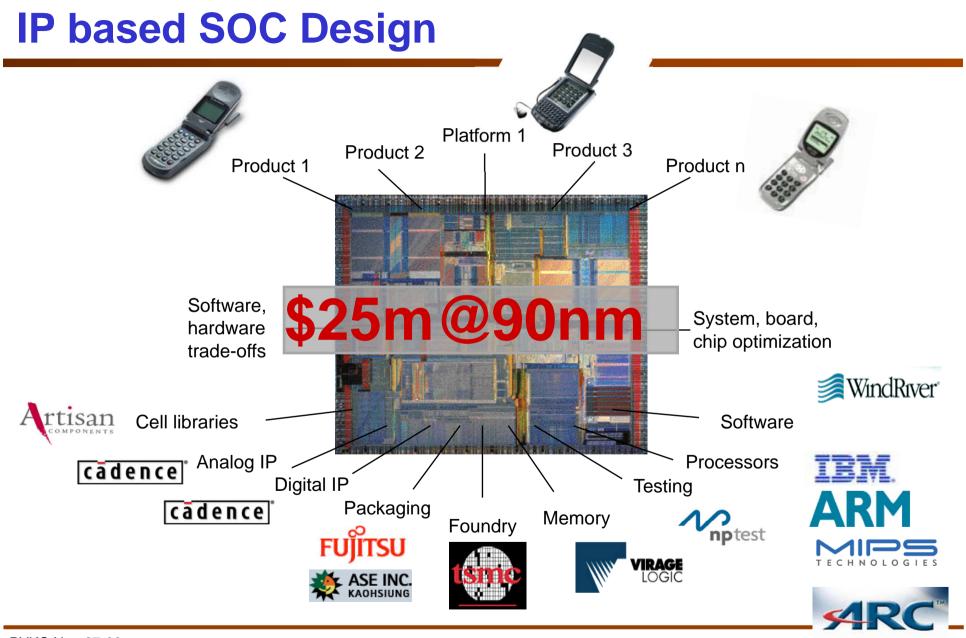
Design Flow (con't)



ASIC design flow. Steps 1-4 are logical design, and steps 5-9 are physical design

ASIC Cell Libraries

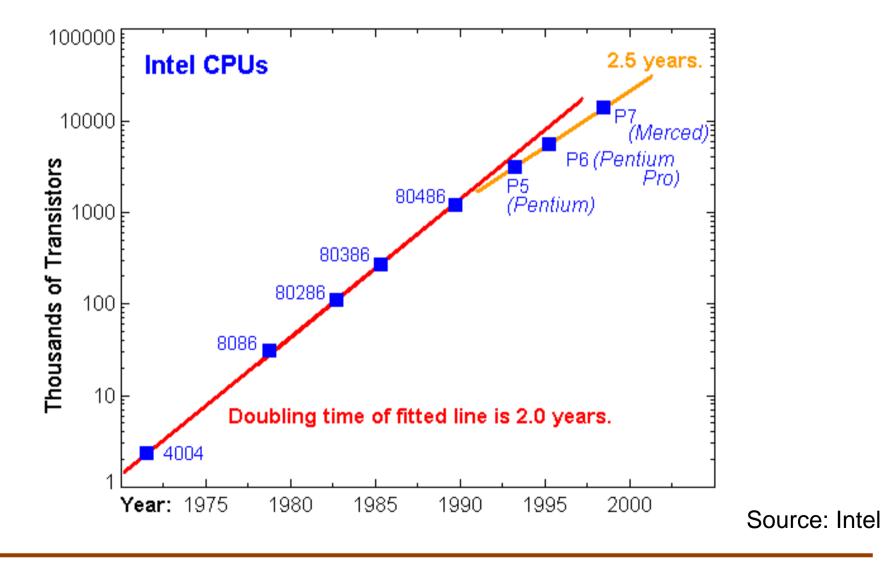
- Use a **design kit** from the **ASIC vendor**
 - Usually a phantom library—the cells are empty boxes, or phantoms, you hand off your design to the ASIC vendor and they perform phantom instantiation (Synopsys CBA)
- Buy an ASIC-vendor library from a library vendor
 - buy-or-build decision. You need a qualified cell library (qualified by the ASIC foundry) If you own the masks (the tooling) you have a customer -owned tooling solution (which is becoming very popular)
- Build your own cell library
 - involves a complex library development process: cell layout ; behavioral model ; Verilog/VHDL model ; timing model ; test strategy ; characterization ; circuit extraction ; process control monitors (PCMs) or drop-ins ; cell schematic ; cell icon ; layout versus schematic (LVS) check; cell icon ; logic synthesis ; retargeting ; wire-load model ; routing model; phantom



Challenges in VLSI

- Gordon Moore, co-founder of Intel, observed in 1965 that number of transistors per square inch in ICs doubled every year.
- In subsequent years, the pace slowed down a bit, but density has doubled approximately every 18 months, and this is the current definition of Moore's Law.
- Most experts, including Moore himself, expect Moore's Law to hold for at least another two decades.

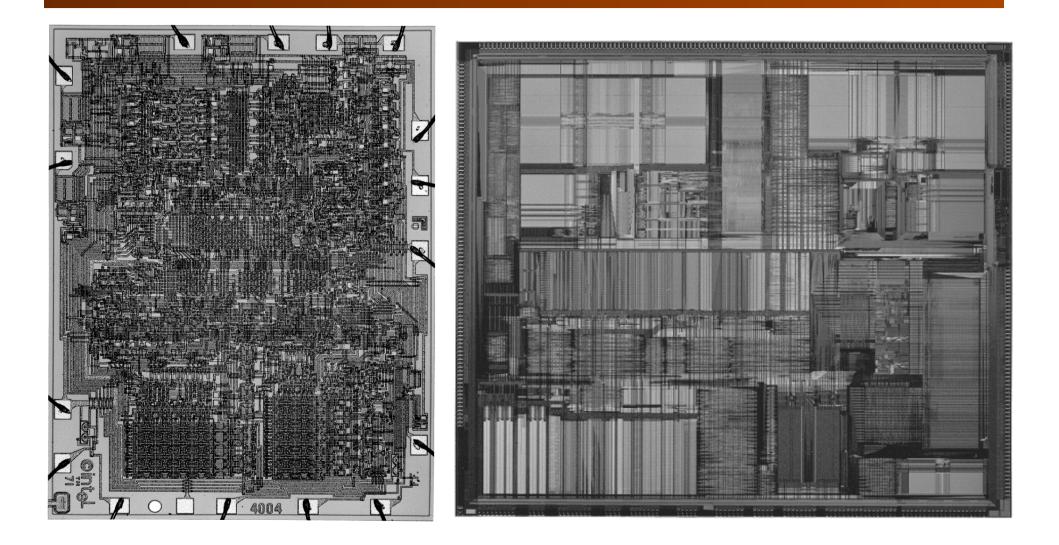
+ Moore's Law



Intel microprocessors

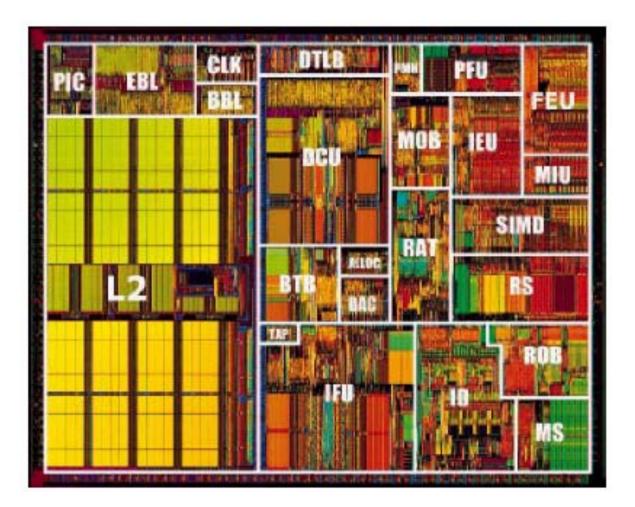
	Year of introduction	Transistors
4004	1971	2,250
8008	1972	2,500
8080	1974	5,000
8086	1978	29,000
286	1982	120,000
386™ processor	1985	275,000
486™ DX processor	1989	1,180,000
Pentium® processor	1993	3,100,000
Pentium II processor	1997	7,500,000
Pentium III processor	1999	24,000,000
Pentium 4 processor	2000	42,000,000

Intel Microprocessor - 4004 & Pentium II

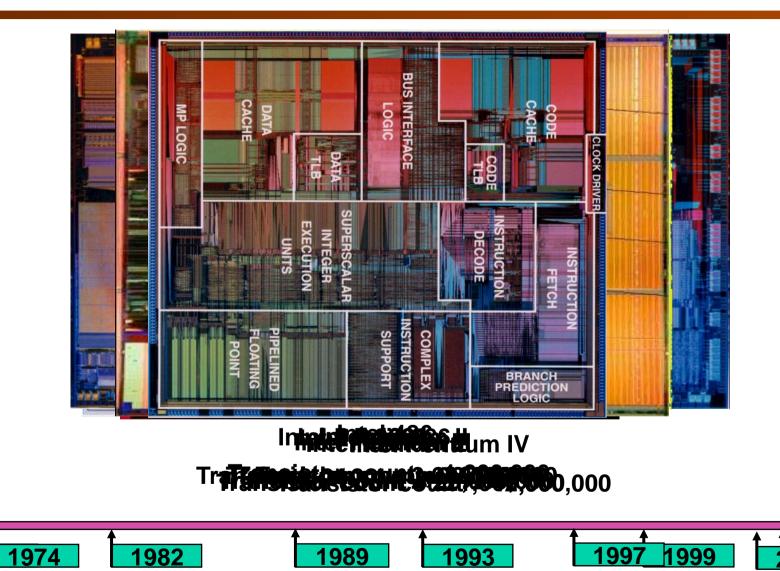


Intel Pentium III

- Intel Pentium III
- 0.18 micron process
- 28 million transistors

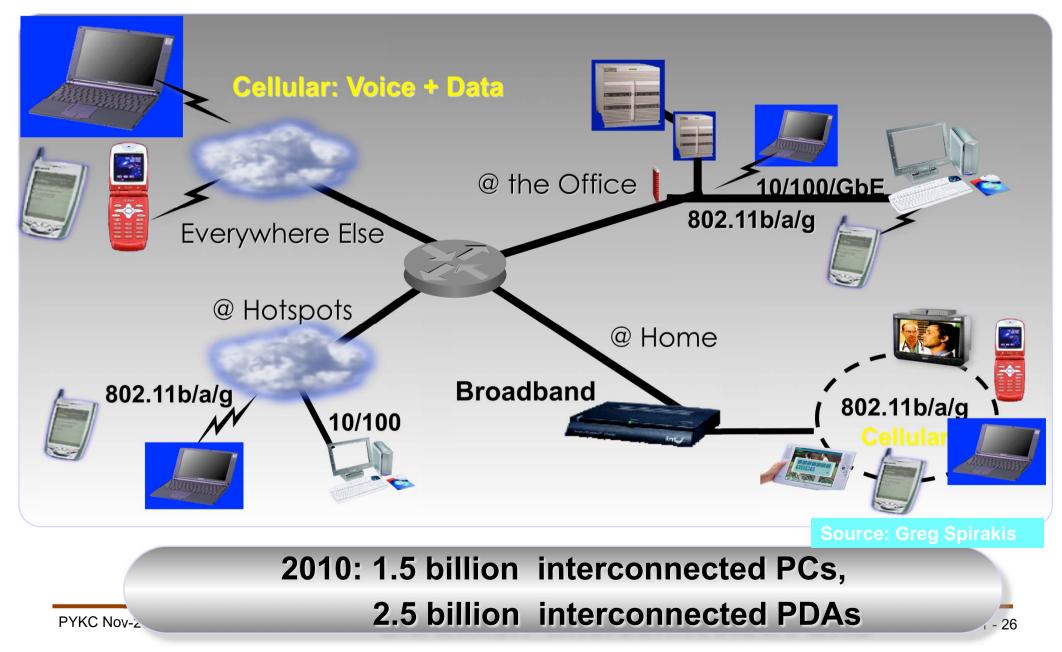


The Complexity Problem



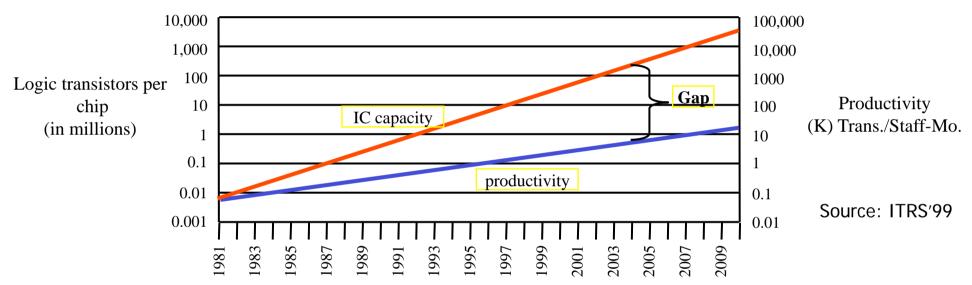
2002

Any Device, Any Time, Anywhere



Very Few Companies Can Design High-End ICs

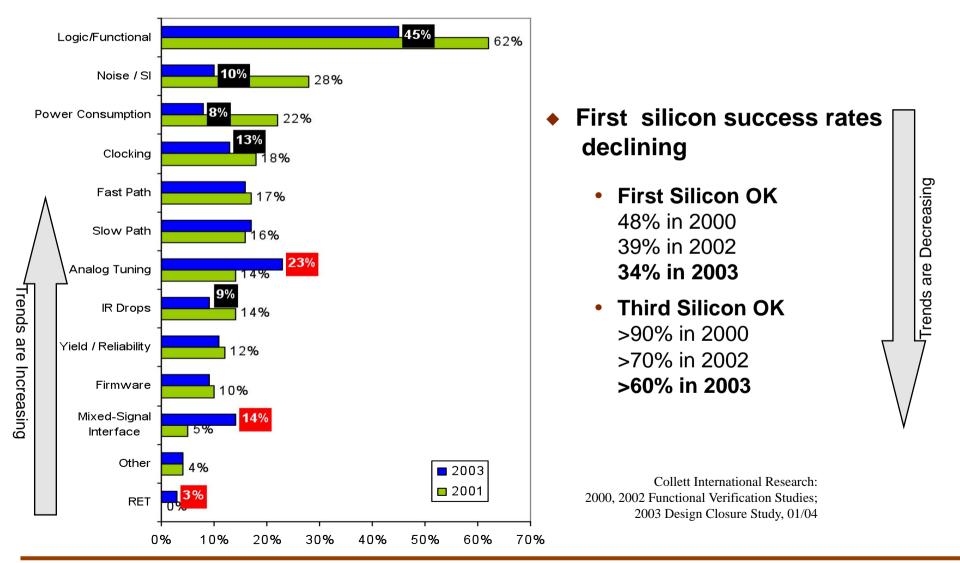
Design productivity gap



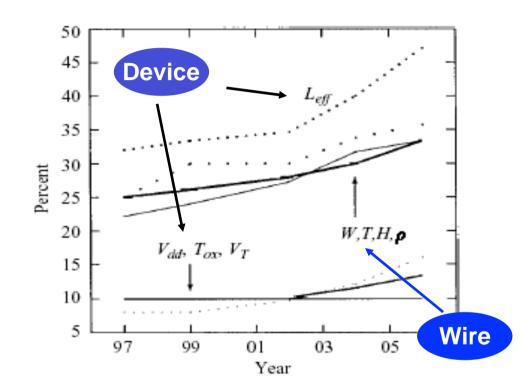
- Designer productivity growing at slower rate
 - ► 1981: 100 designer months \rightarrow ~\$1M
 - ➤ 2002: 30,000 designer months → ~\$300M

Less First Silicon Success

and the Changing Rate of Failures

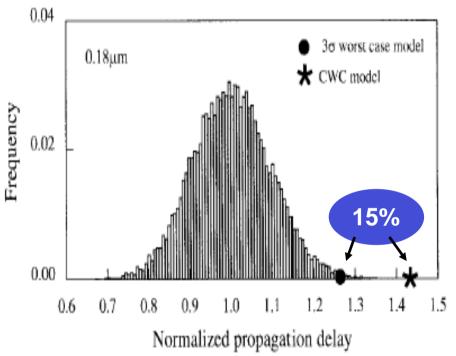


Process Variability Dealing with Uncertainty



Source: "Models of process variations in device and interconnect" by Duane Boning, MIT & Sani Nassif, IBM ARL.

16-bit adder Critical Path delay 0.18µm



"Impact of Unrealistic Worst Case Modeling on the Performance of VLSI circuits in Deep Submicron Region CMOS Technologies"- A.Nardi, A.Neviani, E.Zanoni,M.Quarantelli, IEEE '99

Silicon in 2009

			Density	Access Time
Die Area: 2.5x2.5 cm Voltage: 0.6 V Technology: 0.07 μm	0 5.0 5		(Gbit <mark>s/cm</mark> 2)	(ns)
		DRAM	8.5	10
		DRAM (Logic)	2.5	10
	SRAM (Cache)	0.3	1.5	

	Density	Max. Ave. Power	Clock Rate
	(Mgates/cm2)	(W/cm2)	(GHz)
Custom	25	54	3
Std. Cell	10	27	1.5
Gate Array	5	18	2,1
Single-Mask GA	2.5	12.5	0.7
FPGA	0.4	4.5	0.25

Further Reading

- Moore's Law article
- International Technology Roadmap for Semiconductors (2007 Edition)

http://www.itrs.net/Links/2007ITRS/Home2007.htm

Assignment 1

- Objective: For you to be familiar with the factors that drives the future of integrated circuit technology
- Specification: You are required to read one of two documents: 2007_Design

http://www.itrs.net/Links/2007ITRS/2007_Chapters/2007_Design.pdf

- Deliverables: You are required to prepare a PowerPoint presentation (say for a 5 minutes talk with around 5-6 slides) to explain the document you have read to your fellow engineers
- Deadline: You must complete this by Monday 26 October 2009. You have to submit your slides through the web. Instructions on how to do this will be given to you later. (This is a "tick-box" exercise that you must complete, but will not contribute to your final marks.)